Abstracts

Reliability of Power GaAs FET’s--Au Gates and Al-Au Linked Gates

E.D. Cohen, A.C. Macpherson and A. Christou. "Reliability of Power GaAs FET’s--Au Gates and Al-Au Linked Gates." 1981 Transactions on Microwave Theory and Techniques 29.7 (Jul. 1981 [T-MTT]): 636-642.

An investigation of the reliability of two types of commercial microwave power GaAs FET's has been carried out. Mean-time-to-failure data for a device mounted face-up with Al gates but without an Al-Au couple is presented and similar data for a "flip-chip" mounted Au-refractory gate device is reviewed. The failure mechanisms for both devices are described.

❑ Return to main document.